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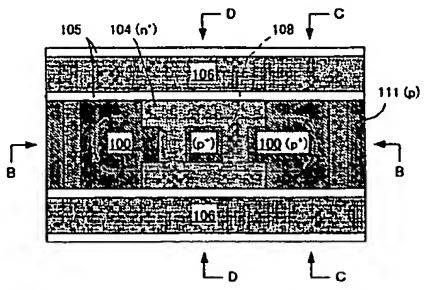
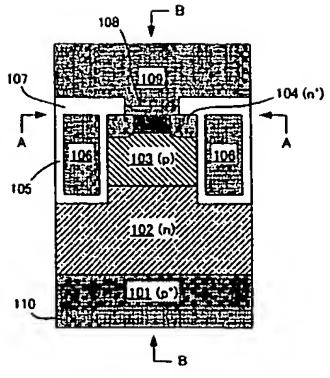
(54) Title: SEMICONDUCTOR DEVICE





(57) Abstract: To present a semiconductor device capable of operating stably even at large current, by lessening current concentration into the corners of contact opening after switching off and suppressing local heat generation without raising the ON voltage. In an insulated gate transistor divided by P field region 111 and gate electrode 106, having N+ emitter region 104 and P+ emitter region 100, and controlling conduction between emitter and collector by voltage applied to gate electrode 106, the shape of contact opening 108 contacting emitter (N+ emitter region 104 and P+ emitter region 100) and emitter electrode is formed of curved lines at four corners. Hence, eliminating right-angle apex, hole current from the field region into the emitter electrode after switching off is prevented from concentrating at one point.

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